100V P-CHANNEL ENHANCEMENT MODE MOSFET
PowerDI5060-8/SWP

Product Summary

BV_{DSS}	$R_{DS(ON)}$	I_D T_C = +25°C
-100V	83mΩ @ V_{GS} = -10V	-20A
	89mΩ @ V_{GS} = -6V	-19A

Description and Applications

This new generation Enhancement Mode MOSFET is designed to minimize $R_{DS(ON)}$ yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- Active clamp switches
- Load switches

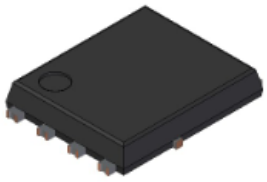
Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test in Production
- High Conversion Efficiency
- Low $R_{DS(ON)}$ – Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- Wettable Flank for Improved Optical Inspections
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/**

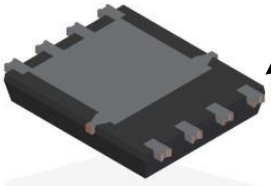
Mechanical Data

- Package: PowerDI®5060-8/SWP
- Package Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.097 grams (Approximate)

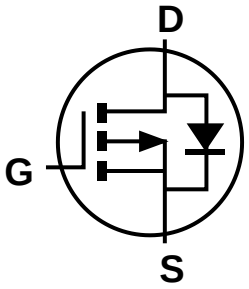
PowerDI5060-8/SWP (Type UX)



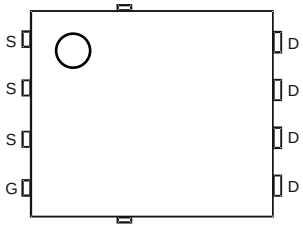
Top View



Bottom View



Internal Schematic



Top View
Pin Configuration

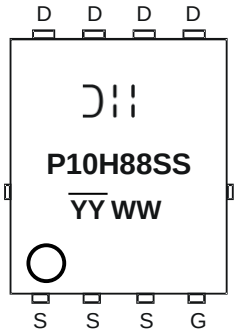
Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMP10H088SPS-13	PowerDI5060-8/SWP (Type UX)	2,500	Tape & Reel

Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

PowerDI5060-8/SWP (Type UX)



= Manufacturer's Marking
P10H88SS = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 23 = 2023)
WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-100	V
Gate-Source Voltage			V_{GSS}	±25	V
Continuous Drain Current (Note 6) V_{GS} = -10V	Steady State	T_C = +25°C T_C = +70°C	I_D	-20 -15	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	-80	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	-20	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I_{SM}	-80	A
Avalanche Current, L = 0.1mH			I_{AS}	-32	A
Repetitive Avalanche Energy, L = 0.1mH			E_{AS}	52	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	2.2	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	56	°C/W
Power Dissipation (Note 6)	P_D	70	W
Thermal Resistance, Junction to Case (Note 6)	$R_{\theta JC}$	1.8	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-100	—	—	V	V_{GS} = 0V, I_D = -1mA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	µA	V_{DS} = -80V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±25V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	-2.0	—	-4.0	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	59	83	mΩ	V_{GS} = -10V, I_D = -4.4A
		—	63	89		V_{GS} = -6V, I_D = -3.6A
Diode Forward Voltage	V_{SD}	—	-0.7	-1.2	V	V_{GS} = 0V, I_S = -1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	1808	—	pF	V_{DS} = -50V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	95	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	47	—	pF	
Gate Resistance	R_g	—	10	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = -10V)	Q_g	—	27.7	—	nC	V_{DS} = -50V, I_D = -4.4A
Total Gate Charge (V_{GS} = -6V)	Q_g	—	17.5	—	nC	
Gate-Source Charge	Q_{gs}	—	6.6	—	nC	
Gate-Drain Charge	Q_{gd}	—	5.8	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	5.4	—	ns	V_{GS} = -10V, V_{DS} = -50V, R_G = 6Ω, I_D = -10A
Turn-On Rise Time	t_R	—	17.4	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	38.6	—	ns	
Turn-Off Fall Time	t_F	—	88.6	—	ns	
Body Diode Reverse Recovery Time	t_{RR}	—	29	—	ns	I_F = -4.4A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q_{RR}	—	34	—	nC	I_F = -4.4A, di/dt = 100A/µs

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
6. Thermal resistance from junction to soldering point (on the exposed drain pad).
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

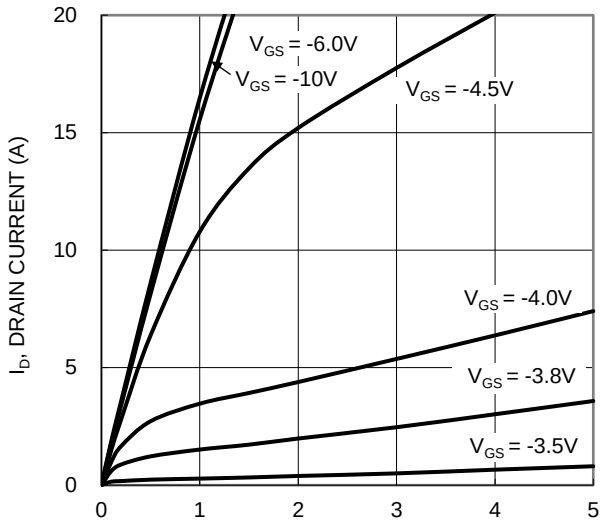


Figure 1. Typical Output Characteristic

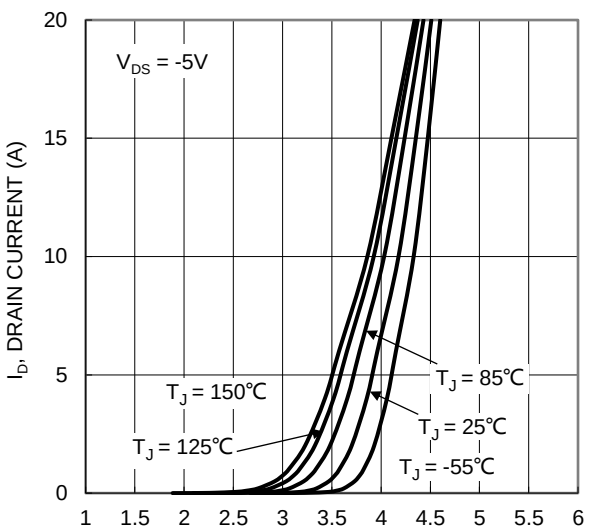


Figure 2. Typical Transfer Characteristic

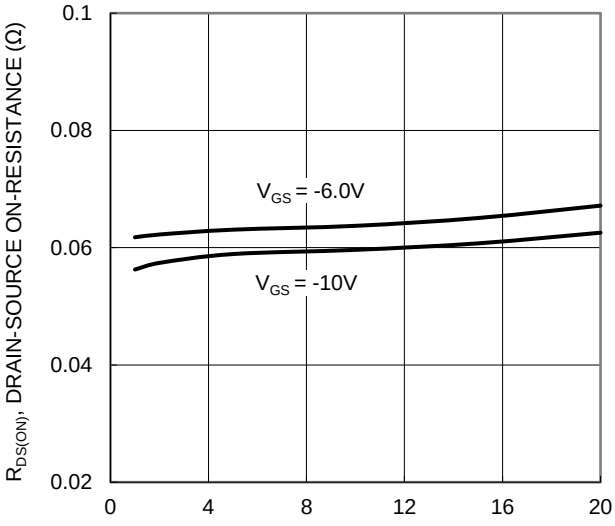


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

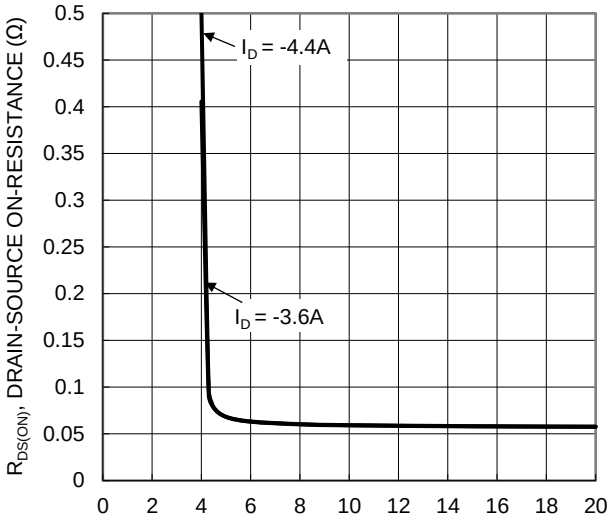


Figure 4. Typical Transfer Characteristic

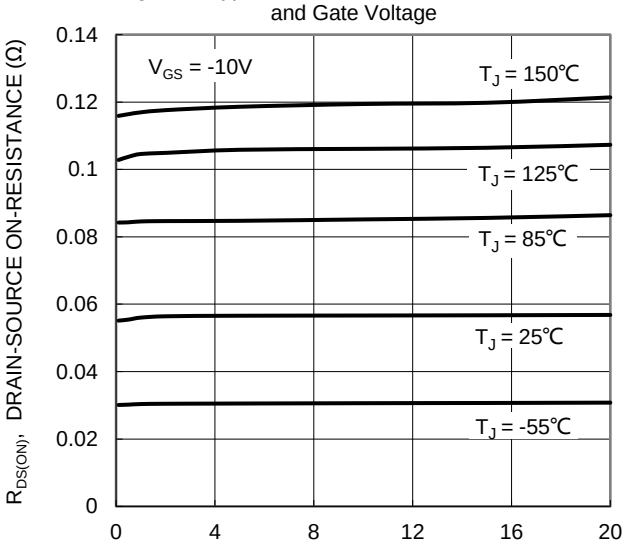


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

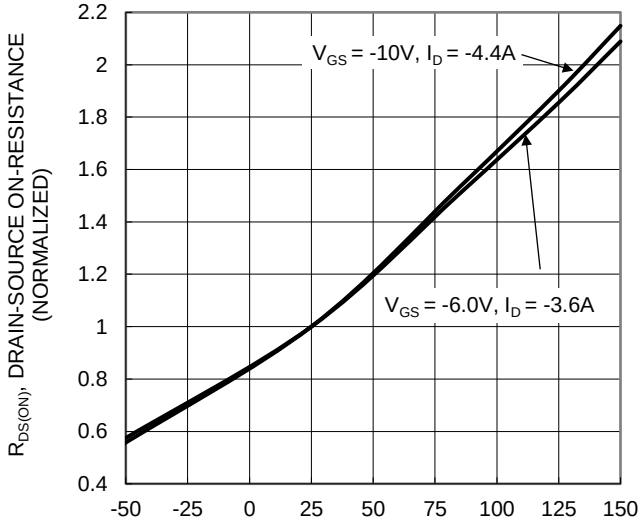


Figure 6. On-Resistance Variation with Junction Temperature

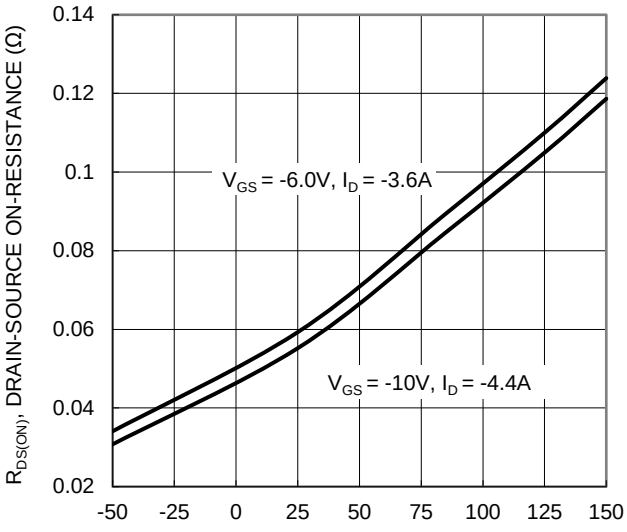


Figure 7. On-Resistance Variation with Junction Temperature

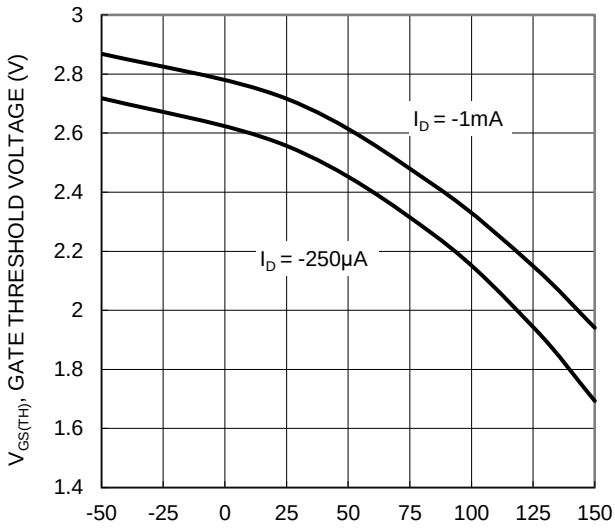


Figure 8. Gate Threshold Variation vs. Junction Temperature

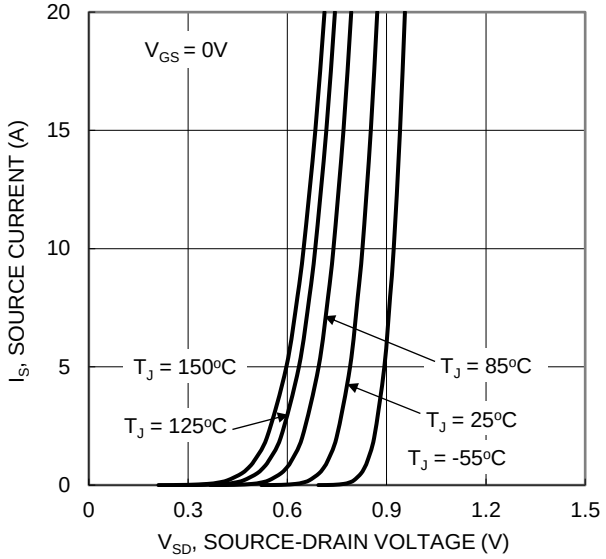


Figure 9. Diode Forward Voltage vs. Current

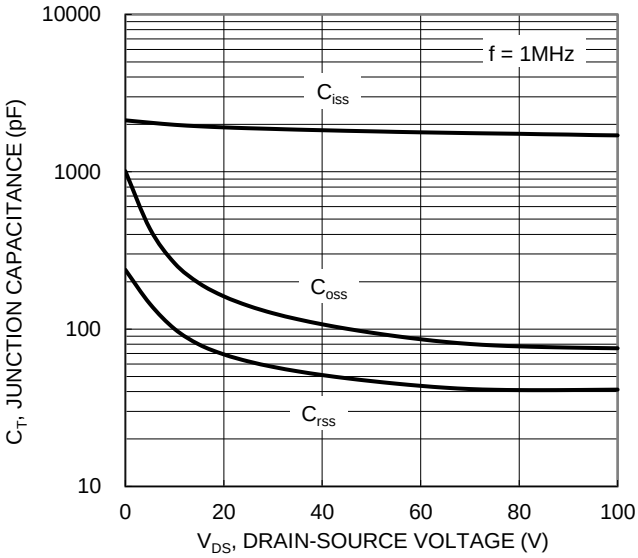


Figure 10. Typical Junction Capacitance

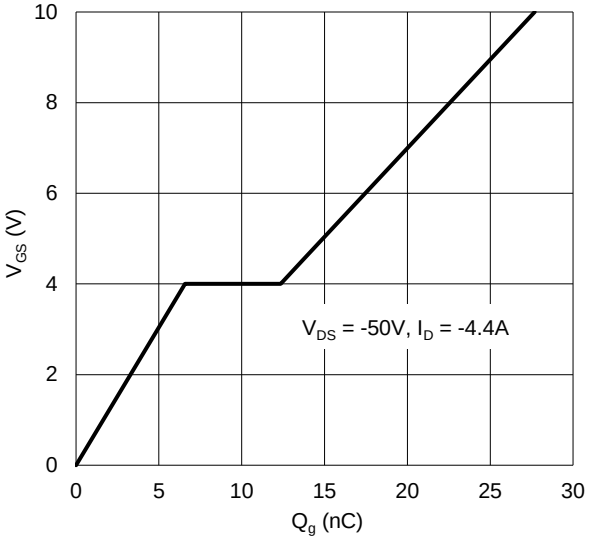


Figure 11. Gate Charge

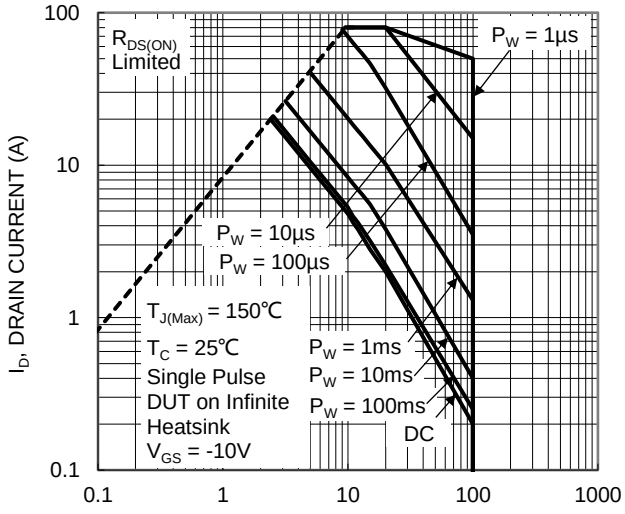


Figure 12. SOA, Safe Operation Area

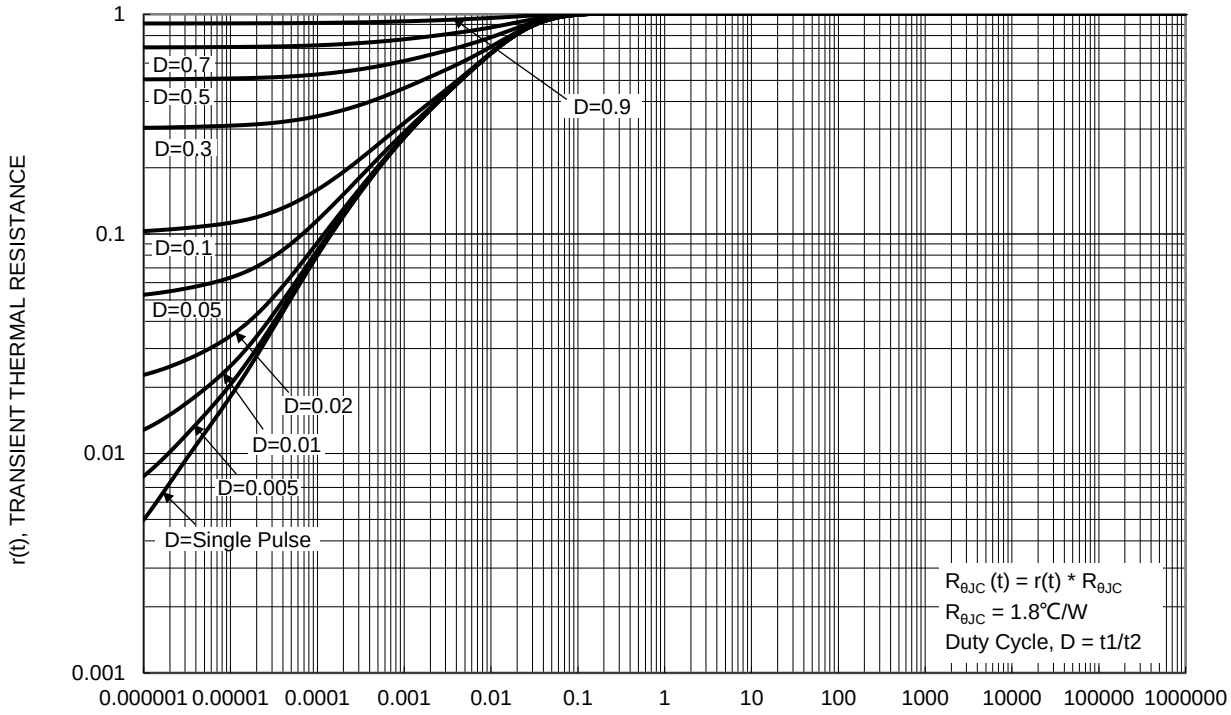
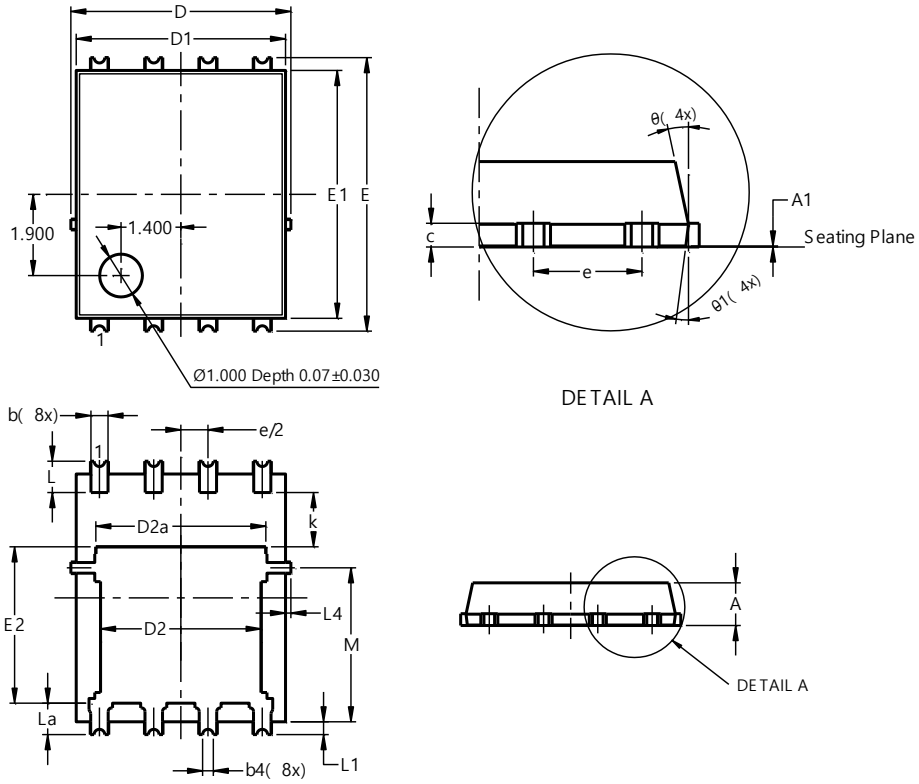


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8/SWP (Type UX)

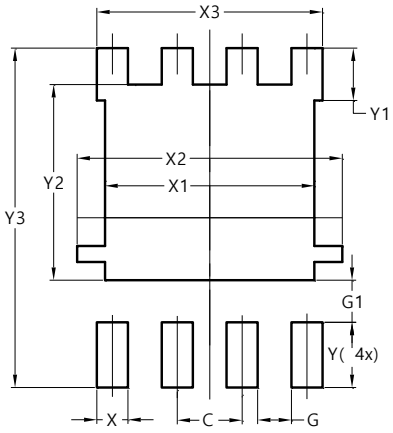


PowerDI5060-8/SWP (Type UX)			
Dim	**Min**	**Max**	**Typ**
A	0.90	1.10	1.00
A1	0	0.05	--
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	0.25REF		
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.56	3.96	3.76
D2a	3.78	4.18	3.98
E	6.40 BSC		
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
e	1.27BSC		
k	1.05	--	--
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
L1a	0.050REF		
L4	0.025	0.225	0.125
M	3.205	4.005	3.605
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8/SWP (Type UX)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	5.190
X3	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

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